

Session 3A, Mon 10:15-11:45, Auditorium

1_227 Self-heating in 4H-SiC avalanche-photodiodes and its impact on spectral responsivity measurements
[Felix Beier \(Fraunhofer IISB, sglux GmbH\)](#)

Session 3B, Mon 10:15-11:45, Convention Hall 1F

4_326 Scalable fabrication and electrical characterization of lateral pin-diodes on 4H-SiC a-plane wafers for functionalization of vsi [Jannik Schwarberg \(FAU Erlangen-Nürnberg\)](#)

Session 5B, Mon 14:45-16:00, Convention Hall 1F

3_244 Impact of current density, accumulated injected charge and temperature on bipolar degradation in 4H-SiC pin-diodes [Rijuta Bagchi](#)

Poster Session 6, Mon 16:15-18:00, Exhibition Hall 1 1F

P22_325 Evaluation of oxide processing steps using contactless corona-based cv measurements [Robin Karhu](#)

P28_514 Minority charge carrier lifetime for evaluating 4H-SiC epitaxial growth by microwave detected photoconductivity decay [Christian Wißgott](#)

P37_305 Reduction of sidewall roughness in SiC trench formation by improvement of photoresist mask
[Alesa Fuchs](#)

P40_391 Extraction of trench sidewall capacitance by linear component separation towards wafer level evaluation [Maximilian Szabo](#)

P53_536 Influence of different contact lengths on 4H-SiC tlm test structures [Maximilian Ley](#)

P52_387 The tunneling field-effect transistor as novel device concept for high-frequency hard-switching power electronics [Jan Frederik Dick \(FAU Erlangen-Nürnberg\)](#)

Poster Session 12, Tue 16:30-18:30, Exhibition Hall 1 1F

P42_276 Utilizing SiO₂ reflow for corner rounding to prevent cracking in passivation layers above 500 °C
[Julien Koerfer](#)

Session 15A, Wed 13:00-14:15, Auditorium

2_438 Parametrization of emitter photoluminescence and color center quantification with neural network
[Christian Gobert](#)

Poster Session 17, Wed 16:30-18:30, Exhibition Hall 1 1F

P09_265 Growth and characterization of “IsoPure” epitaxial layers for quantum applications [Birgit Kallinger](#)

P18_601 Prediction of wafer warpage in 200mm 4H-SiC substrates during subsequent processing by residual stress measurement [Paul Wimmer](#)

P90_493 Transient junction temperature measurement error of SiC MOSFETs in power cycling – influence of cryogenic temperatures [Lukas R. Farnbacher](#)

P79_327 Towards a fully integrated 4H-SiC a-plane quantum-chip – transistors and light emitters
[Jannik Schwarberg \(FAU Erlangen-Nürnberg\)](#)

P76_217 A simulation study of electronic device designs for the control of silicon vacancies in 4H-SiC as spin qubits
[Fabian Jürgen Magerl \(FAU Erlangen-Nürnberg\)](#)

Poster Session 21, Thu 15:00-17:00, Exhibition Hall 1 1F

P22_142 Process-dependent photoluminescence behavior evolution of stacking faults in 4H-SiC [Nadja Kölbel \(FAU Erlangen-Nürnberg\)](#)

P73_386 4H-SiC tunneling light emitter as a light-source for monolithically integrated off-resonant excitation of silicon vacancies [Jan Frederik Dick \(FAU Erlangen-Nürnberg\)](#)